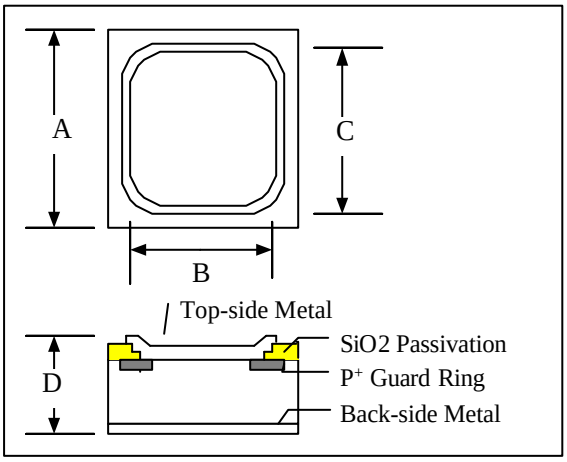
MEMT **Micro-Electro-Magnetical Tech Co.**

SCHOTTKY DIE SPECIFICATION	TYPE: SMBR8100
General Description: 100 V 8 A (Super Low Ir)	Single Anode

ELECTRICAL CHARACTERISTICS	SYM	Spec. Limit	Die Sort	UNIT
DC Blocking Voltage: Ir=1mA(for wafer form)	VRRM	100	105	Volt
Ir=0.5mA (for dice form)				
Average Rectified Forward Current	IFAV	8		Amp
Maximum Instantaneous Forward Voltage				
@ 8 Amperes, Ta=25°C	VF MAX	0.91	0.9	Volt
Maximum Instantaneous Reverse Voltage				
VR= 100 Volt, Ta=25°C	IR MAX	0.08	0.07	mA
Maximum Junction Capacitance @ 0V, 1MHZ	Cj MAX			pF
MAXIMUM RATINGS				
Nonrepetitive Peak Surge Current	IFSM	150		Amp
Operating Junction Temperature	Tj	-65 to +125		°C
Storage Temperatures	TSTG	-65 to +125		°C

Specification apply to die only. Actual performance may degrade when assembled.
MEMT does not guarantee device performance after assembly.
Data sheet information is subjeced to change without notice.

DICE OUTLINE DRAWING



DIM	ITEM	um²	Mil²
A	Die Size	2220	87.40
B	Top Metal Pad Size	2120	83.5
C	Passivation Seal	2140	84.3
D	Thickness (Min)	254	10
	Thickness (Max)	305	12

PS:
(1)Cutting street width is around 80um(3.14mil).
(2)Both of top-side and back-side metals are Ti/Ni/Ag.